Docket No.

211147US99

IN THE TATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

AROON V. TUNGARE ET AL

SERIAL NO:

09/903,784

GAU:

2826

FILED:

JULY 13, 2001

EXAMINER: ERDEM, F.

FOR:

STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR STRUCTURES AND DEVICES

UTILIZING PIEZOELECTRIC MATERIALS

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were submitted in application Serial No. 09/908,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made; reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

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Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,

MAIER & NEWSTADIT, P.C.

Richard L. Treanor

Registration No. 36,379

Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 03/02)

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ATTY DOCKET NO. TRADEN SERIAL NO. Form PTO 1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE 09/903,784 **APPLICANT** LIST OF REFERENCES CITED BY APPLICANT Aroon V. TUNGARE, et al. **FILING DATE GROUP** July 13, 2001 2826 **U.S. PATENT DOCUMENTS** SUB **FILING DATE EXAMINER** DOCUMENT CLASS DATE NAME IF APPROPRIATE CLASS INITIAL NUMBER UT 5,528,209 06/18/96 Macdonald et al. UV 5,998,781 12/07/99 Vawter et al. UW 08/29/00 Ota et al. 6,110,813 6,452,232 B1 09/17/02 Adan UX UY 6,049,110 04/11/00 Koh Hu et al. UΖ 5,559,368 09/24/96 VA 6,392,253 B1 05/21/02 Saxena VΒ 5,585,288 12/17/96 Davis et al. VC 5,268,327 12/07/93 Vernon VD 03/06/01 Nabatame et al. 6,198,119 B1 09/05/00 VΕ Miyata et al. 6,113,225 VF 5,262,659 11/16/93 Grudkowski et al. 05/29/01 Kinsman VG 6,239,012 B1 6,297,598 VΗ 10/02/01 Wang et al. VΙ 2002/140012 10/03/02 Droopad VJ 4,866,489 09/12/89 Yokogawa et al. VΚ 06/27/00 Yokota et al. 6,080,378 VL 04/16/96 Takatani et al. 5,508,554 VM 6,477,285 B1 11/05/02 Shanley VN 4,695,120 09/22/87 Holder VO 5,882,948 03/16/99 Jewell VΡ 5,574,589 11/12/96 Feuer et al. M VQ 5,510,665 04/23/96 Conley VR 4,804,866 02/14/89 Akiyama 5,057,694 vs 10/15/91 ldaka et al. E3 VT 06/03/97 Pique et al. 5,635,453 Roeder et al. VU 5,719,417 02/17/98 5,998,819 12/07/99 Yokoyama et al. **Date Considered** Examiner

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Date Considered

ATTY DOCKET NO. SERIAL NO. U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE Form PTO 1449 (Modified) 211147US99 09/903,784 **APPLICANT** LIST OF REFERENCES CITED BY APPLICANT Aroon V. TUNGARE, et al. **GROUP FILING DATE** July 13, 2001 2826 **U.S. PATENT DOCUMENTS EXAMINER FILING DATE** DOCUMENT SUB **CLASS** DATE NAME IF APPROPRIATE **CLASS** NUMBER INITIAL W 2002/0079576 06/27/02 Seshan VX 5,148,504 09/15/92 Levi et al. 2002/0195610 A1 12/26/02 Klosowiak VY Matsuda ٧Z 5,477,363 12/19/95 WA 5,905,571 05/18/99 Butler et al. 10/29/96 WB 5,570,226 Ota WC 02/11/92 Ishibashi et al. 5,087,829 09/06/01 Saito WD 2001/0020278 A1 WE 6,496,469 B1 12/17/02 Uchizaki WF 5,679,947 10/21/97 Doi et al. Kadowaki et al. WG 2001/0036142 A1 11/01/01 WH 5,446,719 08/29/95 Yoshida et al. 11/03/98 Jiang et al. WI 5,831,960 WJ 5.693,140 12/02/97 McKee et al. WK 04/23/02 Wang et al. 6,376,337 B1 WL 4,177,094 12/04/79 Kroon 06/01/93 Makki et al. WM 5,216,359 10/23/01 Nashimoto et al. WN 6,307,996 B1 12/06/94 WO 5,371,621 Stevens WP 2002/0145168 A1 10/10/02 Bojarczuk, Jr et al. WQ 3,617,951 11/02/71 Anderson 11/17/98 Bevan et al. WR 5,838,053 M ws 5,684,302 11/04/97 Wersing et al. WT 5,959,308 09/28/99 Shichijo et al. 5,362,972 11/08/94 WU Yazawa et al.

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LIST OF REFERENCES CITED BY APPLICANT

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APPLICANT

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	FOREIGN PATENT DOCUMENTS								
	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLAT YES	NO NO				
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CBD	EP 0 860 913	08/26/95	EUROPE						
CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT						
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